

Description

The SX80P10D uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

General Features

$V_{DS} = -100V$ $I_D = -80A$

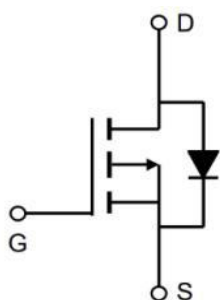
$R_{DS(ON)} < 25m\Omega$ @ $V_{GS} = 10V$

Application

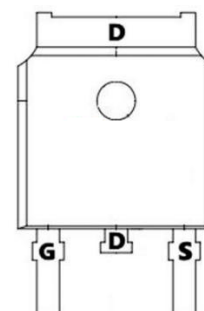
Brushless motor

Load switch

Uninterruptible power supply



TO-252-3L



Absolute Maximum Ratings ($T_c = 25^\circ C$ unless otherwise noted)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	-100	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D @ T_c = 25^\circ C$	Continuous Drain Current, $V_{GS} @ -10V^1$	-80	A
$I_D @ T_c = 100^\circ C$	Continuous Drain Current, $V_{GS} @ -10V^1$	-56	A
I_{DM}	Pulsed Drain Current ²	-300	A
EAS	Single Pulse Avalanche Energy ³	174	mJ
I_{AS}	Avalanche Current	-50	A
$P_D @ T_c = 25^\circ C$	Total Power Dissipation ⁴	280	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ C$
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹	62	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	0.65	$^\circ C/W$

Electrical Characteristics (T_J =25 °C, unless otherwise noted)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
V(BR)DSS	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =-250μA	-100	-	-	V
IDSS	Zero Gate Voltage Drain Current	V _{DS} =-100V, V _{GS} =0V,	-	-	-1.0	μA
IGSS	Gate to Body Leakage Current	V _{DS} =0V, V _{GS} = ±20V	-	-	±100	nA
VGS(th)	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =-250μA	-1.0	-1.6	-2.5	V
RDS(on)	Static Drain-Source on-Resistance	V _{GS} =-10V, I _D =-20A	-	20	25	mΩ
		V _{GS} =-4.5V, I _D =-10A	-	25	30	
Ciss	Input Capacitance	V _{DS} =-50V, V _{GS} =0V, f=1.0MHz	-	4230	-	pF
Coss	Output Capacitance		-	388	-	pF
Crss	Reverse Transfer Capacitance		-	26	-	pF
Q _g	Total Gate Charge	V _{DS} =-50V, I _D =-5A, V _{GS} =-10V	-	80	-	nC
Q _{gs}	Gate-Source Charge		-	15.6	-	nC
Q _{gd}	Gate-Drain("Miller") Charge		-	17.2	-	nC
td(on)	Turn-on Delay Time	V _{DD} =-50V, I _D =-5A, R _G =6Ω, V _{GS} =-10V	-	26	-	ns
tr	Turn-on Rise Time		-	78	-	ns
td(off)	Turn-off Delay Time		-	200	-	ns
tf	Turn-off Fall Time		-	210	-	ns
IS	Maximum Continuous Drain to Source Diode Forward Current		-	-	-80	A
ISM	Maximum Pulsed Drain to Source Diode Forward Current		-	-	-280	A
VSD	Drain to Source Diode Forward Voltage	V _{GS} =0V, I _S =-30A	-	-	-1.2	V
trr	Body Diode Reverse Recovery Time	T _J =25°C, I _F =-5A, dI/dt=100A/μs	-	208	-	ns
Q _{rr}	Body Diode Reverse Recovery Charge		-	560	-	nC

Note :

1、The data tested by surface mounted on a 1 inch 2 FR-4 board with 2OZ copper.

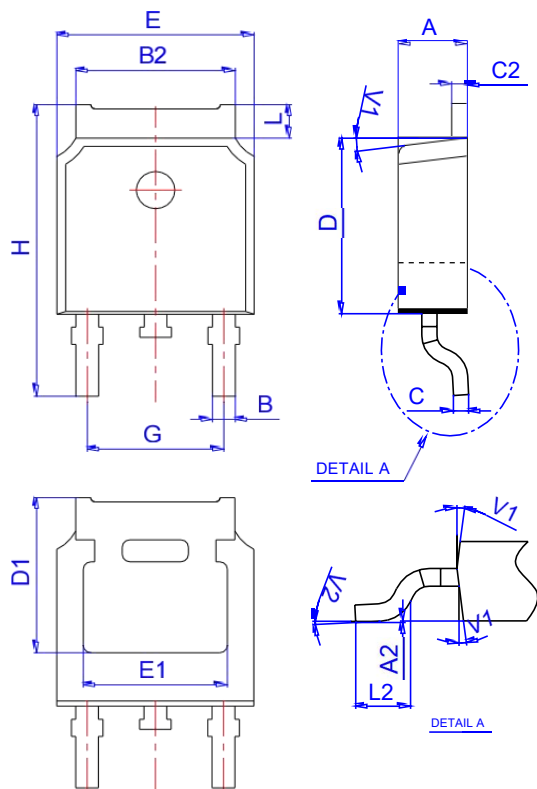
2、The data tested by pulsed , pulse width ≤ 300us , duty cycle ≤ 2%

3、The EAS data shows Max. rating . The test condition is V_{DD} =-72V, V_{GS} =-10V, L=0.1mH, I_{AS} =-50A

4、The power dissipation is limited by 150°C junction temperature

5、The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

Package Mechanical Data:TO-252-3L



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.10		2.50	0.083		0.098
A2	0		0.10	0		0.004
B	0.66		0.86	0.026		0.034
B2	5.18		5.48	0.202		0.216
C	0.40		0.60	0.016		0.024
C2	0.44		0.58	0.017		0.023
D	5.90		6.30	0.232		0.248
D1	5.30REF			0.209REF		
E	6.40		6.80	0.252		0.268
E1	4.63			0.182		
G	4.47		4.67	0.176		0.184
H	9.50		10.70	0.374		0.421
L	1.09		1.21	0.043		0.048
L2	1.35		1.65	0.053		0.065
V1		7°			7°	
V2	0°		6°	0°		6°

Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
TAPING	TO-252-3L		2500